

ISL72028SEH

3.3V Radiation Tolerant CAN Transceiver, with Low Power Shutdown, Split Termination Output

FN8764
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The Intersil [ISL72028SEH](#) is a radiation tolerant 3.3V CAN transceiver that is compatible with the ISO11898-2 standard for applications calling for Controller Area Network (CAN) serial communication in satellites and aerospace communications, and telemetry data processing in harsh industrial environments.

The transceiver can transmit and receive at bus speeds up to 5Mbps. It can drive a 40m cable at 1Mbps per the ISO11898-2 specification. The device is designed to operate over a common-mode range of -7V to +12V with a maximum of 120 nodes. The device has three discrete selectable driver rise/fall time options, a low power shutdown mode and a split termination output.

Receiver (Rx) inputs feature a “full fail-safe” design, which ensures a logic high Rx output if the Rx inputs are floating, shorted, or terminated but undriven.

The ISL72028SEH is available in an 8 Ld hermetic ceramic flatpack and die form that operate across the temperature range of -55 °C to +125 °C. The logic inputs are tolerant with 5V systems.

Other CAN transceivers available are the [ISL72026SEH](#) and [ISL72027SEH](#). For a list of differences see [Table 1 on page 2](#).

Related Literature

- [UG051](#), “ISL7202xSEHEVAL1Z Evaluation Board User Guide”
- [TR018](#), “Single Event Effects (SEE) Testing of the ISL72027SEH CAN Transceiver”
- [TR022](#), “Total Dose Testing of the ISL72026SEH, ISL72027SEH and ISL72028SEH CAN Transceivers”

Features

- Electrically screened to SMD [5962-15228](#)
- ESD protection on all pins. 4kV HBM
- Compatible with ISO11898-2
- Operating supply range 3.0V to 3.6V
- Bus pin fault protection to ±20V
- Undervoltage lockout
- Cold spare: powered down devices/nodes will not affect active devices operating in parallel
- Three selectable driver rise and fall times
- Glitch free bus I/O during power-up and power-down
- Full fail-safe (open, short, terminated/undriven) receiver
- Hi Z input allows for 120 nodes on the bus
- High data rates. up to 5Mbps
- Quiescent supply current 7mA (max)
- Low power shutdown mode 50µA (max)
- -7V to +12V common-mode input voltage range
- 5V tolerant logic inputs
- Thermal shutdown
- Acceptance tested to 75krad(Si) (LDR) wafer-by-wafer
- Radiation tolerance
 - SEL/B immune to LET 60MeV • cm²/mg
 - Low dose rate (0.01rad(Si)/s) 75krad(Si)

Applications

- Satellites and aerospace communications
- Telemetry data processing
- High-end industrial environments
- Harsh environments

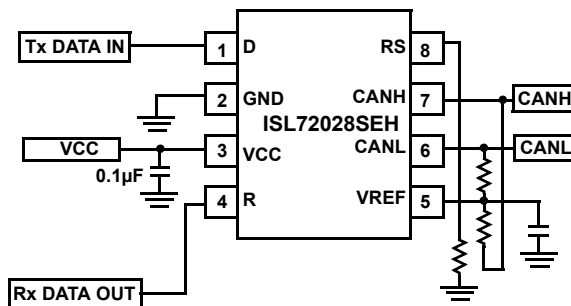


FIGURE 1. TYPICAL APPLICATION

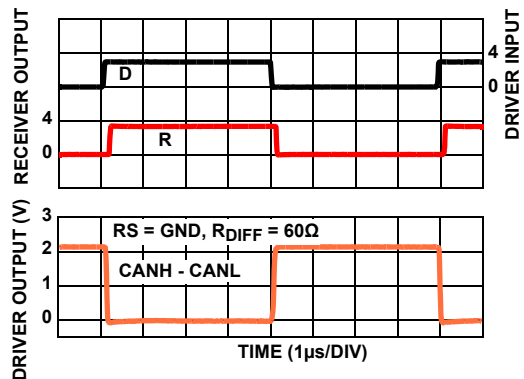


FIGURE 2. FAST DRIVER AND RECEIVER WAVEFORMS

Ordering Information

| ORDERING/SMD NUMBER (Note 1) | PART NUMBER (Note 2) | TEMPERATURE RANGE (°C) | PACKAGE (RoHS Compliant) | PKG DWG # |
|------------------------------|----------------------|------------------------|--------------------------|-----------|
| 5962L1522803VXC | ISL72028SEHVF | -55 to +125 | 8 Ld Ceramic Flat Pack | K8.A |
| N/A | ISL72028SEHF/PROTO | -55 to +125 | 8 Ld Ceramic Flat Pack | K8.A |
| 5962L1522803V9A | ISL72028SEHVX | -55 to +125 | Die | |
| N/A | ISL72028SEHX/SAMPLE | -55 to +125 | Die | |
| N/A | ISL72028SEHEVAL1Z | Evaluation Board | | |

NOTES:

- Specifications for radiation tolerant QML devices are controlled by the Defense Logistics Agency Land and Maritime (DLA). The SMD numbers listed in the Ordering Information table must be used when ordering.
- These Intersil Pb-free Hermetic packaged products employ 100% Au plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations.

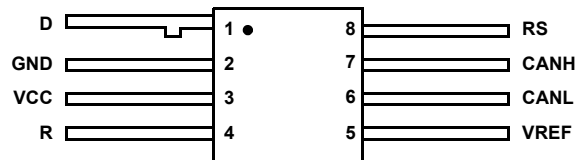
TABLE 1. ISL7202xSEH PRODUCT FAMILY FEATURES TABLE

| SPEC | ISL72026SEH | ISL72027SEH | ISL72028SEH |
|-------------------------------|--------------|--------------|-------------|
| Loopback Feature | Yes | No | No |
| VREF Output | No | Yes | Yes |
| Listen Mode | Yes | Yes | No |
| Shutdown Mode | No | No | Yes |
| VTHRLM | 1150mV (Max) | 1150mV (Max) | N/A |
| VTHFLM | 525mV (Min) | 525mV (Min) | N/A |
| VHYSLM | 50mV (Min) | 50mV (Min) | N/A |
| Supply Current, Listen Mode | 2mA (Max) | 2mA (Max) | N/A |
| Supply Current, Shutdown Mode | N/A | N/A | 50µA (Max) |
| VREF Leakage Current | N/A | ±25µA (Max) | ±25µA (Max) |

N/A: Not Applicable

Pin Configuration

ISL72028SEH
(8 LD CERAMIC FLATPACK)
TOP VIEW



Note: The package lid is tied to ground.

Pin Descriptions

| PIN # | PIN NAME | FUNCTION |
|-------|----------|---|
| 1 | D | CAN Driver Digital Input. The bus states are LOW = Dominant and HIGH = Recessive. Internally tied HIGH. |
| 2 | GND | Ground connection. |
| 3 | VCC | System power supply input (3.0V to 3.6V). The typical voltage for the device is 3.3V. |
| 4 | R | CAN Data Receiver Output. The bus states are LOW = Dominant and HIGH = Recessive. |
| 8 | RS | A resistor to GND from this pin controls the rise and fall time of the CAN output waveform. Drive RS HIGH to put into low power shutdown. |
| 7 | CANH | CAN bus line for low level output |
| 6 | CANL | CAN bus line for high level output |
| 5 | VREF | VCC/2 reference output for split mode termination. |

Equivalent Input and Output Schematic Diagrams

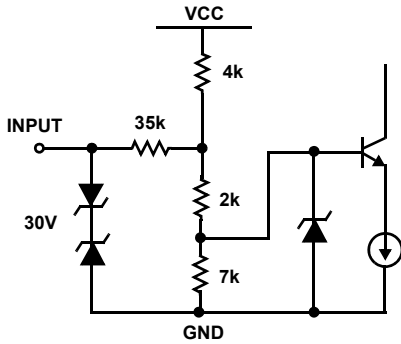


FIGURE 3. CANH AND CANL INPUTS

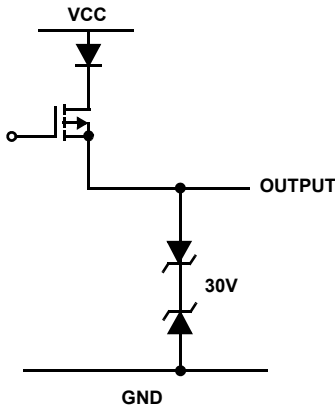


FIGURE 4. CANH OUTPUT

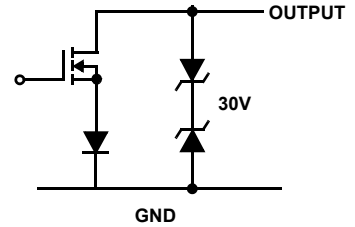


FIGURE 5. CANL OUTPUT

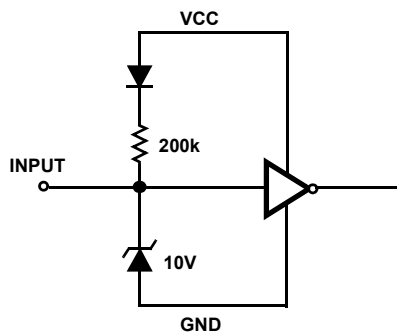


FIGURE 6. D INPUT

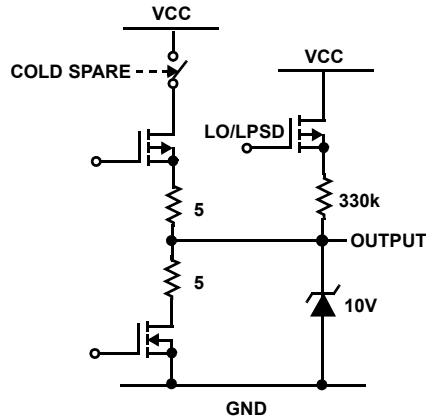


FIGURE 7. R OUTPUT

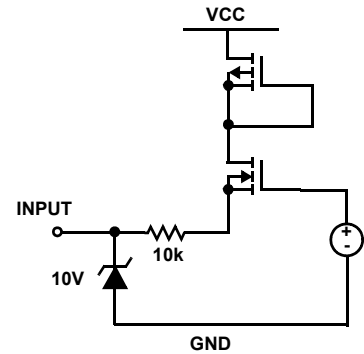


FIGURE 8. RS INPUT

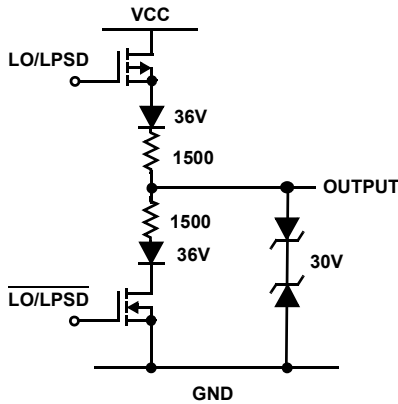


FIGURE 9. VREF

Absolute Maximum Ratings

| | |
|---|---------------|
| VCC to GND With/Without Ion Beam | -0.3V to 5.5V |
| CANH, CANL, VREF Under Ion Beam | ±18V |
| CANH, CANL, VREF | ±20V |
| I/O Voltages | |
| D, R, RS | -0.5V to 7V |
| Receiver Output Current | -10mA to 10mA |
| Output Short-Circuit Duration | Continuous |
| ESD Rating: | |
| Human Body Model | |
| CANH, CANL Bus Pins (Tested per MIL-PRF-883 3015.7) | 4kV |
| All Other Pins (Tested per MIL-PRF-883 3015.7) | 4kV |
| Charged Device Model (Tested per JESD22-C101D) | 750V |
| Machine Model (Tested per JESD22-A115-A) | 200V |

Thermal Information

| | | |
|--|----------------------|----------------------|
| Thermal Resistance (Typical) | θ_{JA} (°C/W) | θ_{JC} (°C/W) |
| 8 Ld FP Package (Notes 3, 4) Direct Attach.. | 39 | 7 |
| Maximum Junction Temperature | +175°C | |
| Storage Temperature Range | -65°C to +150°C | |

Recommended Operating Conditions

| | |
|---|-----------------|
| Temperature Range | -55°C to +125°C |
| VCC Supply Voltage | 3.0V to 3.6V |
| Voltage on CAN I/O | -7V to 12V |
| V _{IH} D Logic Pin | 2V to 5.5V |
| V _{IL} D Logic Pin | 0V to 0.8V |
| I _{OH} Driver (CANH - CANL = 1.5V, V _{CC} = 3.3V) | -40mA |
| I _{OH} Receiver (V _{OH} = 2.4V) | -4mA |
| I _{OL} Driver (CANH - CANL = 1.5V, V _{CC} = 3.3V) | +40mA |
| I _{OL} Receiver (V _{OL} = 0.4V) | +4mA |

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

- θ_{JA} is measured with the component mounted on a high effective thermal conductivity test board (two buried 1oz copper planes) with "direct attach" features package base mounted to PCB thermal land with a 10mil gap fill material having a k of 1W/m-K. See Tech Brief [TB379](#).
- For θ_{JC} , the "case temp" location is the center of the package underside.

Electrical Specifications Test Conditions: V_{CC} = 3.0V to 3.6V; Typicals are at T_A = +25°C (Note 7); unless otherwise specified (Note 5). **Boldface limits apply across the operating temperature range, -55°C to +125°C or over a total ionizing dose of 75krad(Si) at +25°C with exposure at a low dose rate of <10mrad(Si)/s.**

| PARAMETER | SYMBOL | TEST CONDITIONS | TEMP (°C) | MIN (Note 6) | TYP (Note 7) | MAX (Note 6) | UNIT |
|--|----------------------|---|--|--------------|----------------------------|--------------|-------------------|
| DRIVER ELECTRICAL CHARACTERISTICS | | | | | | | |
| Dominant Bus Output Voltage | V _{O(DOM)} | D = 0V, CANH, RS = 0V, Figures 10 and 11 | 3.0V ≤ V _{CC} ≤ 3.6V | Full | 2.25 | 2.85 | V _{CC} V |
| | | D = 0V, CANL, RS = 0V, Figures 10 and 11 | | Full | 0.10 | 0.65 | 1.25 V |
| Recessive Bus Output Voltage | V _{O(REC)} | D = 3V, CANH, RS = 0V, 60Ω and no load, Figures 10 and 11 | 3.0V ≤ V _{CC} ≤ 3.6V | Full | 1.80 | 2.30 | 2.70 V |
| | | D = 3V, CANL, RS = 0V, 60Ω and no load, Figures 10 and 11 | | Full | 1.80 | 2.30 | 2.80 V |
| Dominant Output Differential Voltage | V _{OD(DOM)} | D = 0V, RS = 0V, 3.0V ≤ V _{CC} ≤ 3.6V, Figures 10 and 11 | 3.0V ≤ V _{CC} ≤ 3.6V | Full | 1.5 | 2.2 | 3.0 V |
| | | D = 0V, RS = 0V, 3.0V ≤ V _{CC} ≤ 3.6V, Figures 11 and 12 | | Full | 1.2 | 2.1 | 3.0 V |
| Recessive Output Differential Voltage | V _{OD(REC)} | D = 3V, RS = 0V, 3.0V ≤ V _{CC} ≤ 3.6V, Figures 10 and 11 | 3.0V ≤ V _{CC} ≤ 3.6V, no load | Full | -120 | 0.2 | 12 mV |
| | | D = 3V, RS = 0V, 3.0V ≤ V _{CC} ≤ 3.6V, no load | | Full | -500 | -34 | 50 mV |
| Logic Input High Voltage (D) | V _{IH} | 3.0V ≤ V _{CC} ≤ 3.6V, Note 8 | 3.0V ≤ V _{CC} ≤ 3.6V | Full | 2.0 | - | 5.5 V |
| Logic Input Low Voltage (D) | V _{IL} | 3.0V ≤ V _{CC} ≤ 3.6V, Note 8 | 3.0V ≤ V _{CC} ≤ 3.6V | Full | 0 | - | 0.8 V |
| High Level Input Current (D) | I _{IH} | D = 2.0V, 3.0V ≤ V _{CC} ≤ 3.6V | 3.0V ≤ V _{CC} ≤ 3.6V | Full | -30 | -3 | 30 μA |
| Low Level Input Current (D) | I _{IL} | D = 0.8V, 3.0V ≤ V _{CC} ≤ 3.6V | 3.0V ≤ V _{CC} ≤ 3.6V | Full | -30 | -7 | 30 μA |
| RS Input Voltage for Low Power Shutdown Mode | V _{IN(RS)} | 3.0V ≤ V _{CC} ≤ 3.6V | 3.0V ≤ V _{CC} ≤ 3.6V | Full | 0.75xV_{CC} | 1.9 | 5.5 V |

Electrical Specifications Test Conditions: $V_{CC} = 3.0V$ to $3.6V$; Typical values are at $T_A = +25^\circ C$ (Note 7); unless otherwise specified (Note 5). **Boldface limits apply across the operating temperature range, $-55^\circ C$ to $+125^\circ C$ or over a total ionizing dose of $75krad(Si)$ at $+25^\circ C$ with exposure at a low dose rate of $<10mrads(Si)/s$.** (Continued)

| PARAMETER | SYMBOL | TEST CONDITIONS | TEMP ($^\circ C$) | MIN (Note 6) | TYP (Note 7) | MAX (Note 6) | UNIT |
|--|---------------|---|------------------------|-----------------|-----------------|-----------------|------------|
| Output Short-Circuit Current | I_{OSC} | $V_{CANH} = -7V$, $CANL = OPEN$, $3.0V \leq V_{CC} \leq 3.6V$, Figure 18 | Full | -250 | -100 | - | mA |
| | | $V_{CANH} = +12V$, $CANL = OPEN$, $3.0V \leq V_{CC} \leq 3.6V$, Figure 18 | Full | - | 0.4 | 1.0 | mA |
| | | $V_{CANL} = -7V$, $CANH = OPEN$, $3.0V \leq V_{CC} \leq 3.6V$, Figure 18 | Full | -1.0 | -0.4 | - | mA |
| | | $V_{CANL} = +12V$, $CANH = OPEN$, $3.0V \leq V_{CC} \leq 3.6V$, Figure 18 | Full | - | 100 | 250 | mA |
| Thermal Shutdown Temperature | T_{SHDN} | $3.0V < V_{IN} < 3.6V$ | - | - | 163 | - | $^\circ C$ |
| Thermal Shutdown Hysteresis | T_{HYS} | $3.0V < V_{IN} < 3.6V$ | - | - | 12 | - | $^\circ C$ |
| RECEIVER ELECTRICAL CHARACTERISTICS | | | | | | | |
| Input Threshold Voltage (Rising) | V_{THR} | $RS = 0V, 10k, 50k$, (recessive to dominant), Figures 14 and 15 | Full | - | 750 | 900 | mV |
| Input Threshold Voltage (Falling) | V_{THF} | $RS = 0V, 10k, 50k$, (dominant to recessive), Figures 14 and 15 | Full | 500 | 650 | - | mV |
| Input Hysteresis | V_{HYS} | $(V_{THR} - V_{THF})$, $RS = 0V, 10k, 50k$, Figures 14 and 15 | Full | 40 | 90 | - | mV |
| Receiver Output High Voltage | V_{OH} | $I_O = -4mA$ | Full | 2.4 | $V_{CC} - 0.2$ | - | V |
| Receiver Output Low Voltage | V_{OL} | $I_O = +4mA$ | Full | - | 0.2 | 0.4 | V |
| Input Current for CAN Bus | I_{CAN} | $CANH$ or $CANL$ at $12V$, $D = 3V$, other bus pin at $0V$, $RS = 0V$ | Full | - | 420 | 500 | μA |
| | | $CANH$ or $CANL$ at $12V$, $D = 3V$, $V_{CC} = 0V$, other bus pin at $0V$, $RS = 0V$ | Full | - | 150 | 250 | μA |
| | | $CANH$ or $CANL$ at $-7V$, $D = 3V$, other bus pin at $0V$, $RS = 0V$ | Full | -400 | -300 | - | μA |
| | | $CANH$ or $CANL$ at $-7V$, $D = 3V$, $V_{CC} = 0V$, other bus pin at $0V$, $RS = 0V$ | Full | -150 | -85 | - | μA |
| Input Capacitance ($CANH$ or $CANL$) | C_{IN} | Input to GND, $D = 3V$, $RS = 0V$ | 25 | - | 35 | - | pF |
| Differential Input Capacitance | C_{IND} | Input to input, $D = 3V$, $RS = 0V$ | 25 | - | 15 | - | pF |
| Input Resistance ($CANH$ or $CANL$) | R_{IN} | Input to GND, $D = 3V$, $RS = 0V$ | Full | 20 | 40 | 50 | k Ω |
| Differential Input Resistance | R_{IND} | Input to input, $D = 3V$, $RS = 0V$ | Full | 40 | 80 | 100 | k Ω |
| SUPPLY CURRENT | | | | | | | |
| Supply Current, Low Power Shutdown Mode | $I_{CC(LPS)}$ | $RS = D = V_{CC}$, $3.0V \leq V_{CC} \leq 3.6V$, Note 9 | Full | - | 20 | 50 | μA |
| Supply Current, Dominant | $I_{CC(DOM)}$ | $D = RS = 0V$, no load, $3.0V \leq V_{CC} \leq 3.6V$ | Full | - | 5 | 7 | mA |
| Supply Current, Recessive | $I_{CC(REC)}$ | $D = V_{CC}$, $RS = 0V$, no load, $3.0V \leq V_{CC} \leq 3.6V$ | Full | - | 2.6 | 5.0 | mA |
| COLD SPARING BUS CURRENT | | | | | | | |
| $CANH$ Leakage Current | $I_L(CANH)$ | $V_{CC} = 0.2V$, $CANH = -7V$ or $12V$, $D = V_{CC}$, $CANL = float$, $RS = 0V$ | Full | -25 | -4 | 25 | μA |
| $CANL$ Leakage Current | $I_L(CANL)$ | $V_{CC} = 0.2V$, $CANL = -7V$ or $12V$, $D = V_{CC}$, $CANH = float$, $RS = 0V$ | Full | -25 | -4 | 25 | μA |
| VREF Leakage Current | $I_L(VREF)$ | $V_{CC} = 0.2V$, $V_{REF} = -7V$ or $12V$, $D = V_{CC}$ | Full | -25.00 | 0.01 | 25.00 | μA |
| DRIVER SWITCHING CHARACTERISTICS | | | | | | | |
| Propagation Delay LOW to HIGH | t_{PDLH1} | $RS = 0V$, Figure 13 | Full | - | 75 | 150 | ns |
| Propagation Delay LOW to HIGH | t_{PDLH2} | $RS = 10k\Omega$, Figure 13 | Full | - | 520 | 850 | ns |
| Propagation Delay LOW to HIGH | t_{PDLH3} | $RS = 50k\Omega$, Figure 13 | Full | - | 850 | 1400 | ns |
| Propagation Delay HIGH to LOW | t_{PDHL1} | $RS = 0V$, Figure 13 | Full | - | 80 | 155 | ns |

Electrical Specifications Test Conditions: $V_{CC} = 3.0V$ to $3.6V$; Typicals are at $T_A = +25^\circ C$ (Note 7); unless otherwise specified (Note 5). **Boldface limits apply across the operating temperature range, $-55^\circ C$ to $+125^\circ C$ or over a total ionizing dose of 75krad(Si) at $+25^\circ C$ with exposure at a low dose rate of $<10\text{mrad(Si)/s}$. (Continued)**

| PARAMETER | SYMBOL | TEST CONDITIONS | TEMP ($^\circ C$) | MIN (Note 6) | TYP (Note 7) | MAX (Note 6) | UNIT |
|--|----------------|--|------------------------|---------------------------------------|-----------------|---------------------------------------|---------|
| Propagation Delay HIGH to LOW | t_{PDHL2} | RS = 10k Ω , Figure 13 | Full | - | 460 | 800 | ns |
| Propagation Delay HIGH to LOW | t_{PDHL3} | RS = 50k Ω , Figure 13 | Full | - | 725 | 1300 | ns |
| Output Skew | t_{SKEW1} | RS = 0V, ($ t_{PHL} - t_{PLH} $), Figure 13 | Full | - | 5 | 50 | ns |
| Output Skew | t_{SKEW2} | RS = 10k Ω , ($ t_{PHL} - t_{PLH} $), Figure 13 | Full | - | 60 | 510 | ns |
| Output Skew | t_{SKEW3} | RS = 50k Ω , ($ t_{PHL} - t_{PLH} $), Figure 13 | Full | - | 110 | 800 | ns |
| Output Rise Time | t_{r1} | RS = 0V, (fast speed) Figure 13 | Full | 20 | 55 | 100 | ns |
| Output Fall Time | t_{f1} | | Full | 10 | 25 | 75 | ns |
| Output Rise Time | t_{r2} | RS = 10k Ω , (medium speed - 250Kbps) Figure 13 | Full | 200 | 400 | 780 | ns |
| Output Fall Time | t_{f2} | | Full | 175 | 300 | 500 | ns |
| Output Rise Time | t_{r3} | RS = 50k Ω , (slow speed - 125Kbps) Figure 13 | Full | 400 | 700 | 1400 | ns |
| Output Fall Time | t_{f3} | | Full | 300 | 650 | 1000 | ns |
| Total Loop Delay, Driver Input to Receiver Output, Recessive to Dominant | $t_{(LOOP1)}$ | RS = 0V, Figure 16 | Full | - | 115 | 210 | ns |
| | | RS = 10k Ω , Figure 16 | Full | - | 550 | 875 | ns |
| | | RS = 50k Ω , Figure 16 | Full | - | 850 | 1400 | ns |
| Total Loop Delay, Driver Input to Receiver Output, Dominant to Recessive | $t_{(LOOP2)}$ | RS = 0V, Figure 16 | Full | - | 130 | 270 | ns |
| | | RS = 10k Ω , Figure 16 | Full | - | 500 | 825 | ns |
| | | RS = 50k Ω , Figure 16 | Full | - | 750 | 1300 | ns |
| Low Power Shutdown to Valid Dominant Time | t_{LPS_DOM} | Figure 17 , Note 9 | Full | - | 6 | 15 | μs |
| RECEIVER SWITCHING CHARACTERISTICS | | | | | | | |
| Propagation Delay LOW to HIGH | t_{PLH} | Figure 14 | Full | - | 50 | 110 | ns |
| Propagation Delay HIGH to LOW | t_{PHL} | Figure 14 | Full | - | 50 | 110 | ns |
| Rx Skew | t_{SKEW1} | $ t_{PHL} - t_{PLH} $, Figure 14 | Full | - | 2 | 35 | ns |
| Rx Rise Time | t_r | Figure 14 | Full | - | 2 | - | ns |
| Rx Fall Time | t_f | Figure 14 | Full | - | 2 | - | ns |
| VREF/RS PIN CHARACTERISTICS | | | | | | | |
| VREF Pin Voltage | VREF | $-5\mu A < I_{REF} < 5\mu A$ | Full | 0.45xV_C c | 1.6 | 0.55xV_C c | V |
| | | $-50\mu A < I_{REF} < 50\mu A$ | Full | 0.40xV_C c | 1.6 | 0.60xV_C c | V |
| RS Pin Input Current | $I_{RS(H)}$ | RS = 0.75xV _{CC} | Full | -10.0 | -0.2 | - | μA |
| | $I_{RS(L)}$ | V _{RS} = 0V | Full | -450 | -125 | 0 | μA |

NOTES:

- All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to device ground unless otherwise specified.
- Parameters with MIN and/or MAX limits are 100% tested at $-55^\circ C$, $+25^\circ C$ and $+125^\circ C$, unless otherwise specified.
- Typical values are at 3.3V. Parameters with a single entry in the "TYP" column apply to 3.3V. Typical values shown are not guaranteed.
- Parameter included in functional testing.
- Performed during the 100% screening operations across the full operating temperature range. Not performed as part of TCI Group E and Group C. Radiation characterization testing performed as part of the initial release and any major changes in design.

Test Circuits and Waveforms

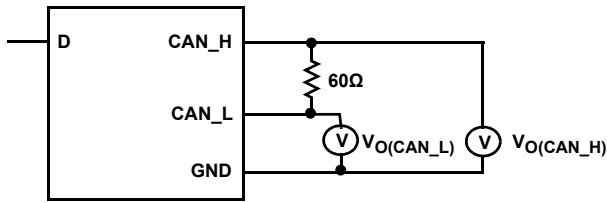


FIGURE 10. DRIVER TEST CIRCUIT

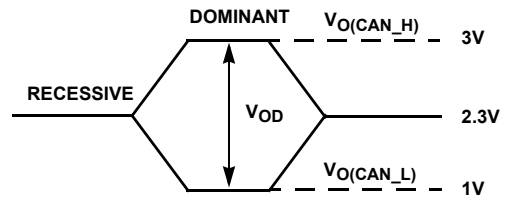


FIGURE 11. DRIVER BUS VOLTAGE DEFINITIONS

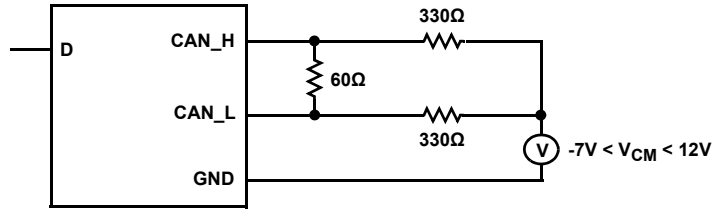
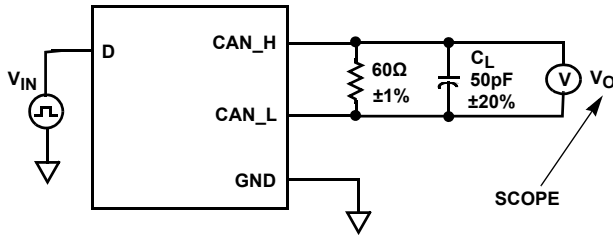


FIGURE 12. DRIVER COMMON-MODE CIRCUIT



$V_{IN} = 125\text{kHz}$, 0V to V_{CC} , Duty Cycle 50%, $t_r = t_f \leq 6\text{ns}$, $Z_O = 50\Omega$
 C_L includes fixture and instrumentation capacitance

FIGURE 13A. DRIVER TIMING TEST CIRCUIT

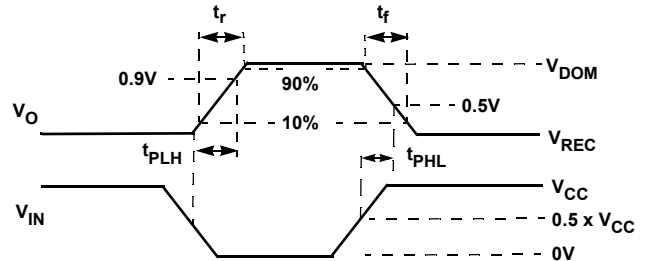


FIGURE 13B. DRIVER TIMING MEASUREMENT POINTS

FIGURE 13. DRIVER TIMING

Test Circuits and Waveforms (Continued)

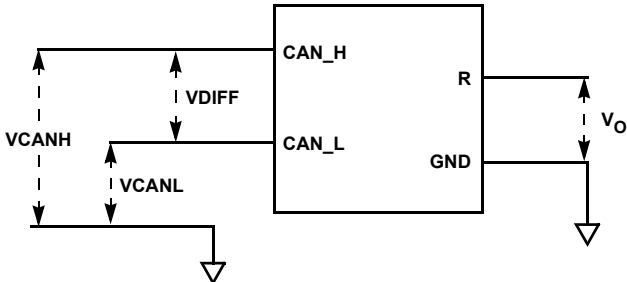
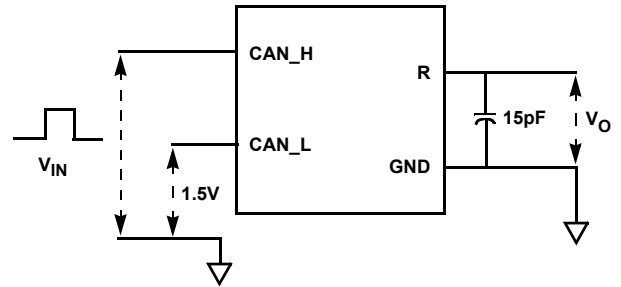


FIGURE 14A. RECEIVER VOLTAGE DEFINITIONS



$V_{IN} = 125\text{kHz}$, Duty Cycle 50%, $t_r = t_f \leq 6\text{ns}$, $Z_O = 50\Omega$
 C_L includes test setup capacitance

FIGURE 14B. RECEIVER TEST CIRCUIT

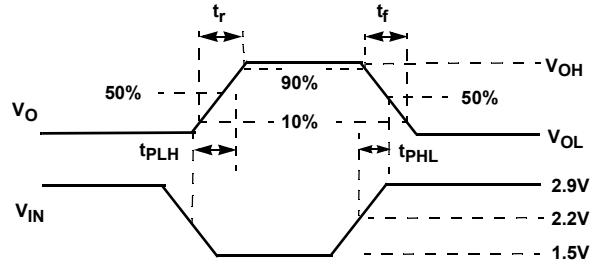


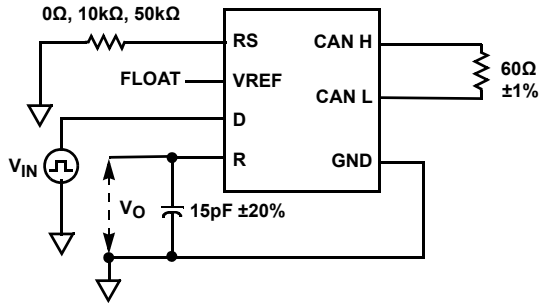
FIGURE 14C. RECEIVER TEST MEASUREMENT POINTS

FIGURE 14. RECEIVER TEST

| INPUT | | OUTPUT | MEASURED |
|-------|-------|--------|----------|
| VCANH | VCANL | R | VDIFF |
| -6.1V | -7V | L | 900mV |
| 12V | 11.1V | L | 900mV |
| -1V | -7V | L | 6V |
| 12V | 6V | L | 6V |
| -6.5V | -7V | H | 500mV |
| 12V | 11.5V | H | 500mV |
| -7V | -1V | H | 6V |
| 6V | 12V | H | 6V |

FIGURE 15. DIFFERENTIAL INPUT VOLTAGE THRESHOLD TEST

Test Circuits and Waveforms (Continued)



$V_{IN} = 125\text{kHz}$, Duty Cycle 50%, $t_r = t_f \leq 6\text{ns}$

FIGURE 16A. TOTAL LOOP DELAY TEST CIRCUIT

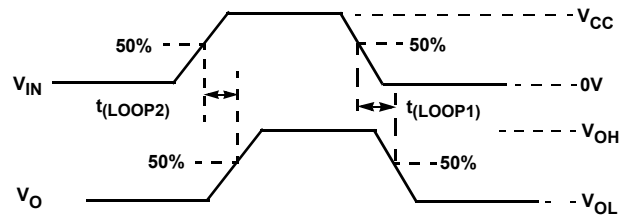
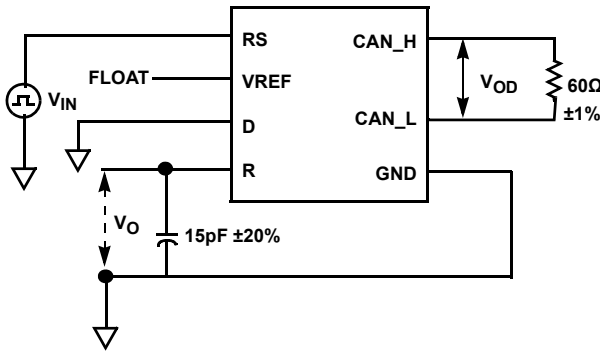


FIGURE 16B. TOTAL LOOP DELAY MEASUREMENT POINTS

FIGURE 16. TOTAL LOOP DELAY



$V_{IN} = 125\text{kHz}$, 0V to V_{CC} , Duty Cycle 50%, $t_r = t_f \leq 6\text{ns}$.

FIGURE 17A. LOW POWER SHUTDOWN TO DOMINANT TIME CIRCUIT

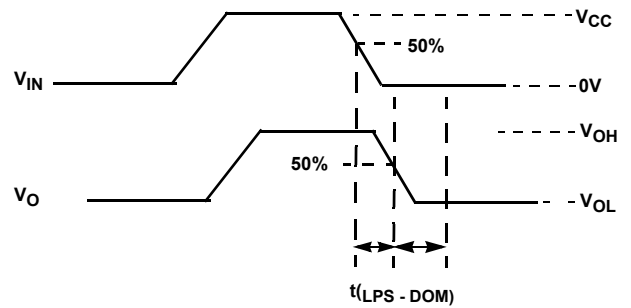


FIGURE 17B. LOW POWER SHUTDOWN TO DOMINANT TIME MEASUREMENT POINTS

FIGURE 17. LOW POWER SHUTDOWN TO DOMINANT TIME

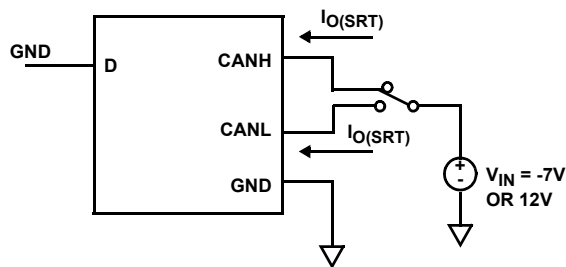


FIGURE 18A. OUTPUT SHORT-CIRCUIT CURRENT CIRCUIT

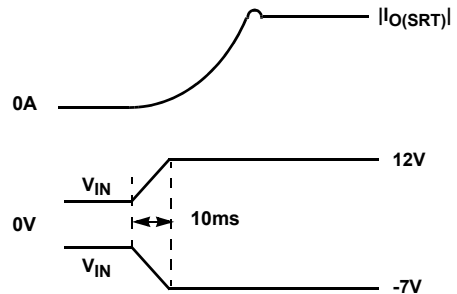


FIGURE 18B. OUTPUT SHORT-CIRCUIT CURRENT WAVEFORMS

FIGURE 18. OUTPUT SHORT CIRCUIT

Functional Description

Overview

The Intersil ISL72028SEH is a 3.3V radiation tolerant CAN transceiver that is compatible with the ISO11898-2 standard for use in CAN (Controller Area Network) serial communication systems.

The device performs transmit and receive functions between the CAN controller and the CAN differential bus. It can transmit and receive at bus speeds of up to 5Mbps. It is designed to operate over a common-mode range of -7V to +12V with a maximum of 120 nodes. The device is capable of withstanding $\pm 20V$ on the CANH and CANL bus pins outside of ion beam and $\pm 16V$ under ion beam.

Slope Adjustment

The output driver rise and fall time has three distinct selections that may be chosen by using a resistor from the RS pin to GND. Connecting the RS pin directly to GND results in output switching times that are the fastest, limited only by the drive capability of the output stage. $RS = 10k\Omega$ provides for a typical slew rate of $8V/\mu s$ and $RS = 50k\Omega$ provides for a typical slew rate of $4V/\mu s$.

Putting a high logic level to the RS pin places the device in a low power shutdown mode. The protocol controller uses this mode to switch between low power shutdown mode and normal transmit mode.

Cable Length

The device can work per ISO11898 specification with a 40m cable and stub length of 0.3m and 60 nodes at 1Mbps. This is greater than the ISO requirement of 30 nodes. The cable type specified is twisted pair (shielded or unshielded) with a characteristic impedance of 120Ω . Resistors equal to this are to be terminated at both ends of the cable. Stubs should be kept as short as possible to prevent reflections.

Cold Spare

High reliability system designers implementing data communications have to be sensitive to the potential for single point failures. To mitigate the risk of a failure, they will use redundant bus transceivers in parallel. In this arrangement, both active and quiescent devices can be present simultaneously on the bus. The quiescent devices are powered down for cold spare and do not affect the communication of the other active nodes.

To achieve this, a powered down transceiver ($V_{CC} < 200mV$) has a resistance between the VREF pin or the CANH pin or CANL pin and the VCC supply rail of $>480k\Omega$ (max) with a typical resistance $>2M\Omega$. The resistance between CANH and CANL of a powered-down transceiver has a typical resistance of $80k\Omega$.

Low Power Shutdown Mode

When a high level is applied to the RS pin, the device enters the low power shutdown mode in which the driver and receiver are switched off to conserve power. The bus pins are at High Z and R pin will be at logic high. In low power shutdown the transceiver draws $50\mu A$ (max) of current.

A low level on the RS pin brings the device back to operation.

Using 3.3V Devices in 5V Systems

Looking at the differential voltage of both the 3.3V and 5V devices, the differential voltage is the same, the recessive common-mode output is the same. The dominant common-mode output voltage is slightly lower than the 5V counterparts. The receiver specs are also the same. Though the electrical parameters appear compatible, it is advised that necessary system testing be performed to verify interchangeable operation.

Split Mode Termination

The VREF pin provides a $V_{CC}/2$ output voltage for split mode termination. The VREF pin has the same ESD protection, short circuit protection and common-mode operating range as the bus pins.

The split mode termination technique is shown in [Figure 19](#).

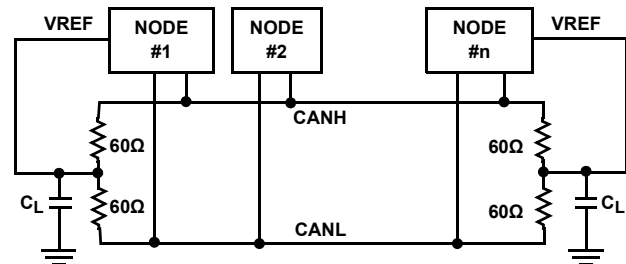


FIGURE 19. SPLIT TERMINATION

It is used to stabilize the bus voltage at $V_{CC}/2$ and prevent it from drifting to a high common-mode voltage during periods of inactivity. The technique improves the electromagnetic compatibility of a network. The split mode termination is put at each end of the bus.

The C_L capacitor between the two 60Ω resistors, filters unwanted high frequency noise to ground. The resistors should have a tolerance of 1% or better and the two resistors should be carefully matched to provide the most effective EMI immunity. A typical value of C_L for a high speed CAN network is $4.7nF$, which generates a 3dB point at 1.1Mbps. The capacitance value used is dependent on the signaling rate of the network.

Typical Performance Curves

$C_L = 15\text{pF}$, $T_A = +25^\circ\text{C}$; unless otherwise specified.

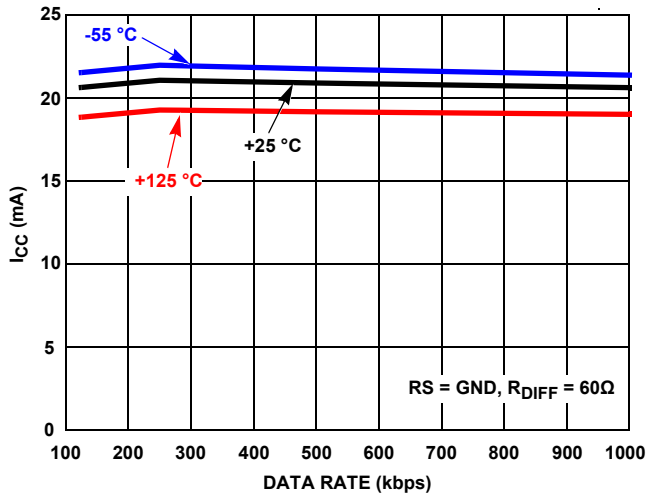


FIGURE 20. SUPPLY CURRENT vs FAST DATA RATE vs TEMPERATURE

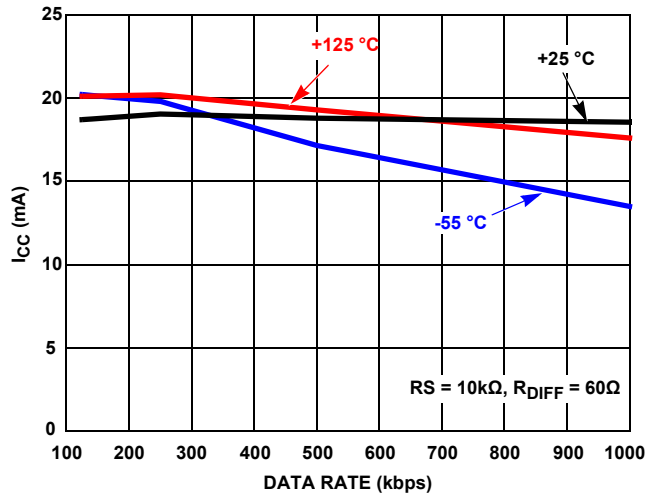


FIGURE 21. SUPPLY CURRENT vs MEDIUM DATA RATE vs TEMPERATURE

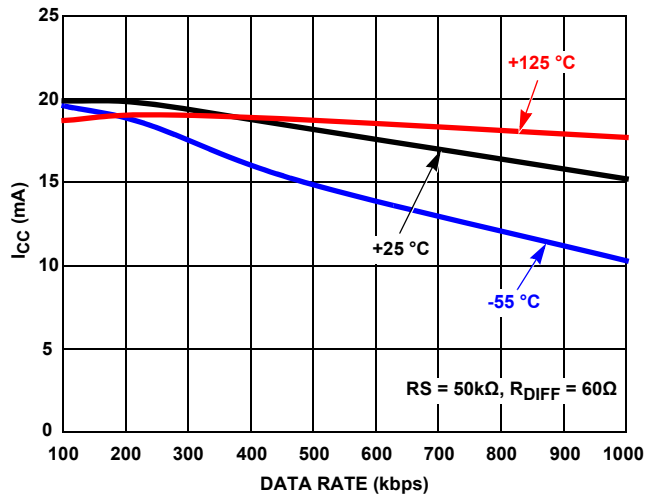


FIGURE 22. SUPPLY CURRENT vs SLOW DATA RATE vs TEMPERATURE

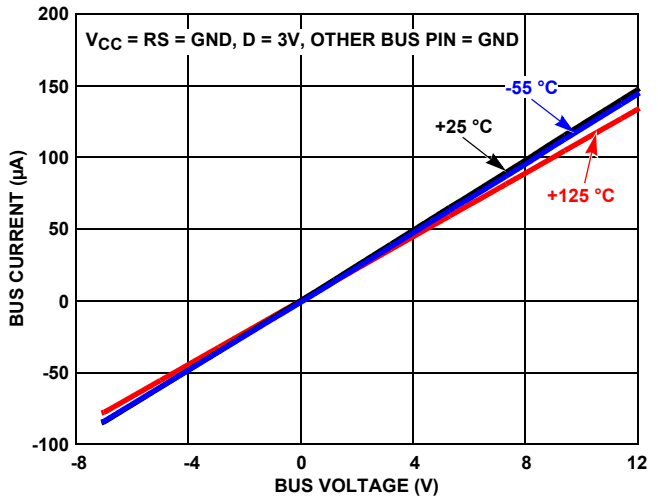


FIGURE 23. BUS PIN LEAKAGE vs V_{CM} AT $V_{CC} = 0V$

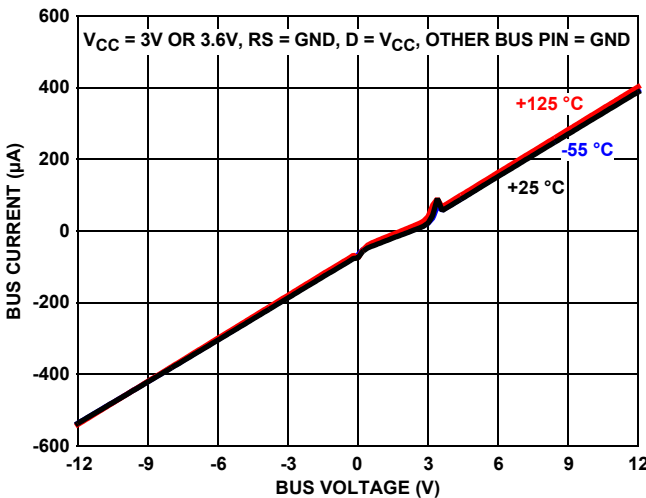


FIGURE 24. BUS PIN LEAKAGE vs $\pm 12V$ V_{CM}

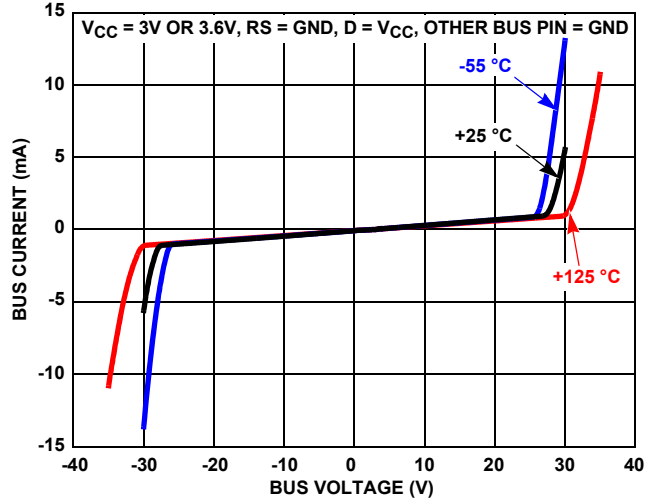


FIGURE 25. BUS PIN LEAKAGE vs $\pm 35V$ V_{CM}

Typical Performance Curves $C_L = 15\text{pF}$, $T_A = +25^\circ\text{C}$; unless otherwise specified. (Continued)

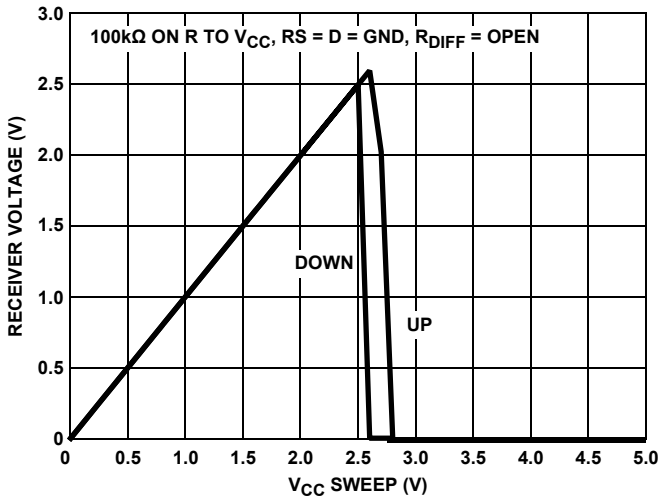


FIGURE 26. V_{CC} UNDERVOLTAGE LOCKOUT

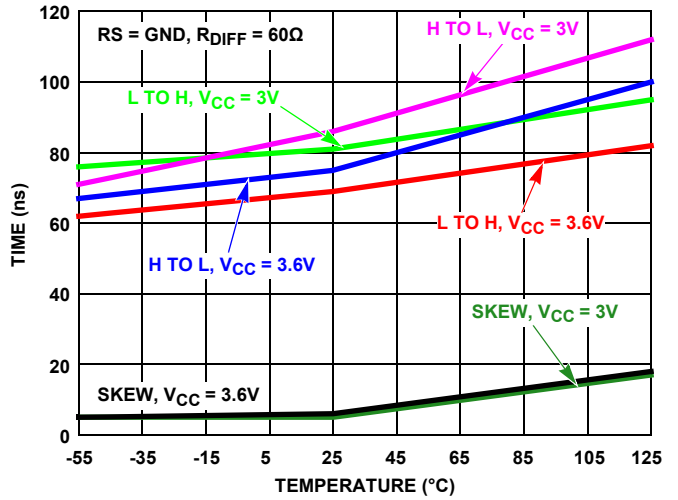


FIGURE 27. TRANSMITTER PROPAGATION DELAY AND SKEW vs TEMPERATURE AT FAST SPEED

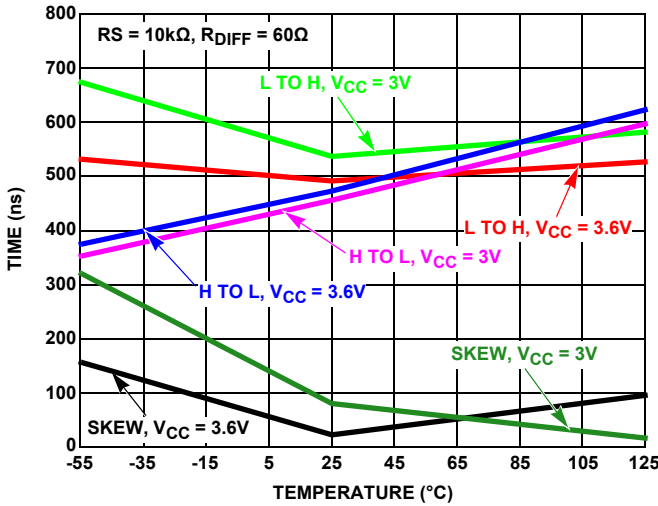


FIGURE 28. TRANSMITTER PROPAGATION DELAY AND SKEW vs TEMPERATURE AT MEDIUM SPEED

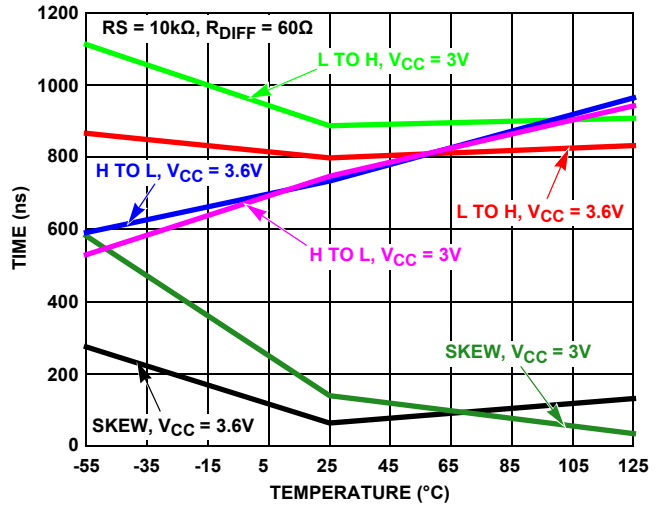


FIGURE 29. TRANSMITTER PROPAGATION DELAY AND SKEW vs TEMPERATURE AT SLOW SPEED

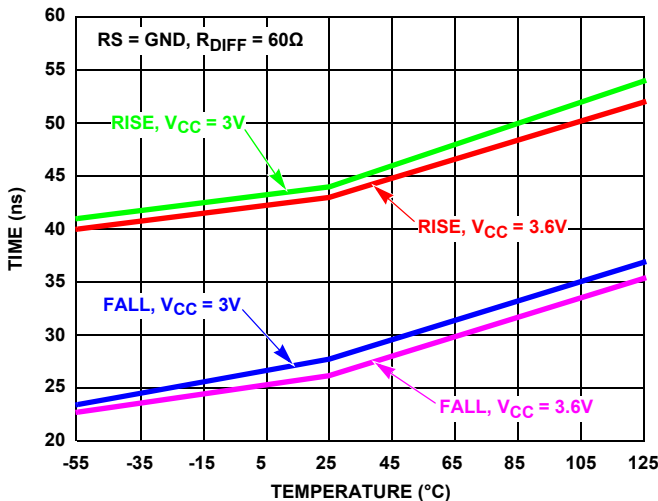


FIGURE 30. TRANSMITTER RISE AND FALL TIMES vs TEMPERATURE AT FAST SPEED

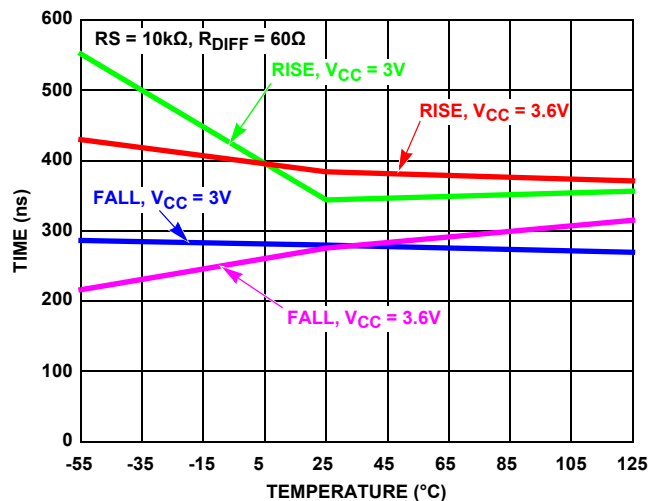


FIGURE 31. TRANSMITTER RISE AND FALL TIMES vs TEMPERATURE AT MEDIUM SPEED

Typical Performance Curves $C_L = 15\text{pF}$, $T_A = +25^\circ\text{C}$; unless otherwise specified. (Continued)

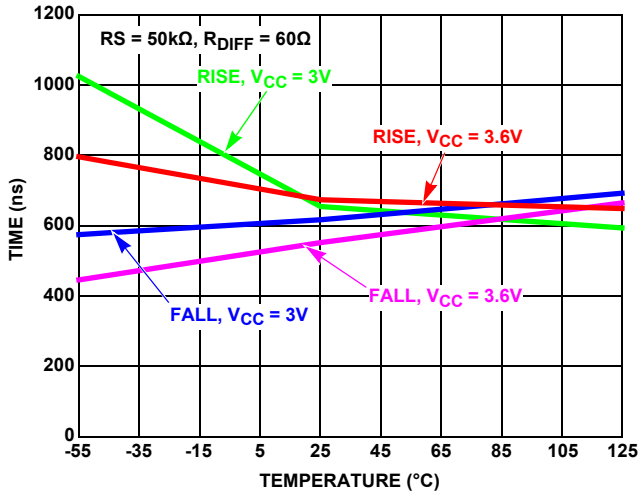


FIGURE 32. TRANSMITTER RISE AND FALL TIMES vs TEMPERATURE AT SLOW SPEED

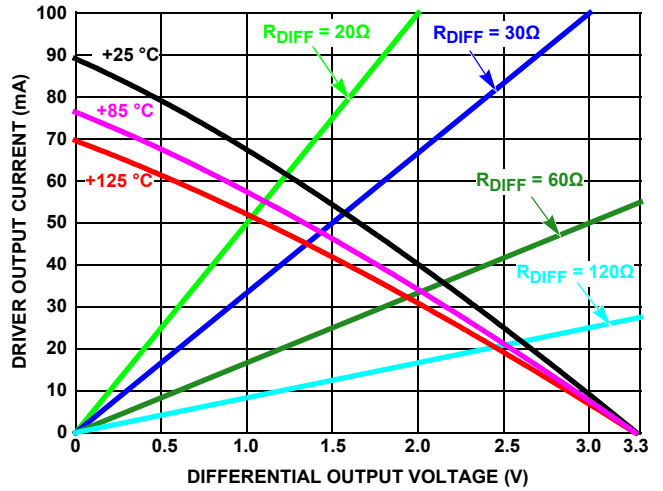


FIGURE 33. DRIVER OUTPUT CURRENT vs DIFFERENTIAL OUTPUT VOLTAGE

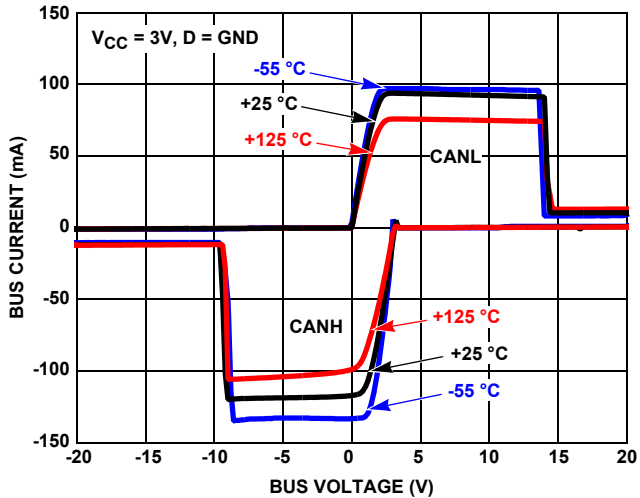


FIGURE 34. DRIVER OUTPUT CURRENT vs SHORT CIRCUIT VOLTAGE vs TEMPERATURE

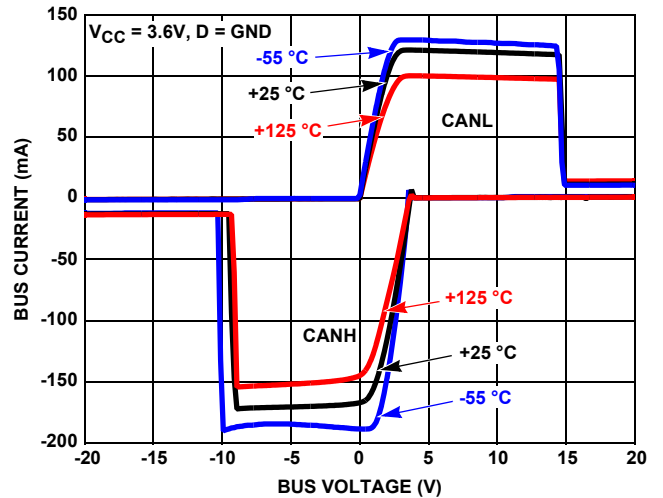


FIGURE 35. DRIVER OUTPUT CURRENT vs SHORT CIRCUIT VOLTAGE vs TEMPERATURE

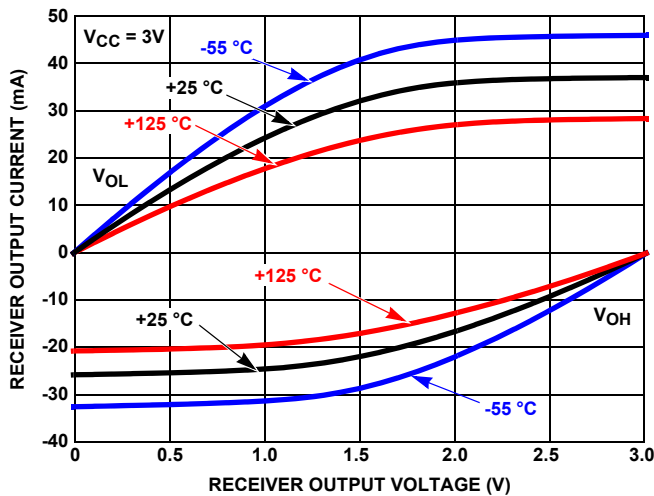


FIGURE 36. RECEIVER OUTPUT CURRENT vs RECEIVER OUTPUT VOLTAGE AT $V_{CC} = 3\text{V}$

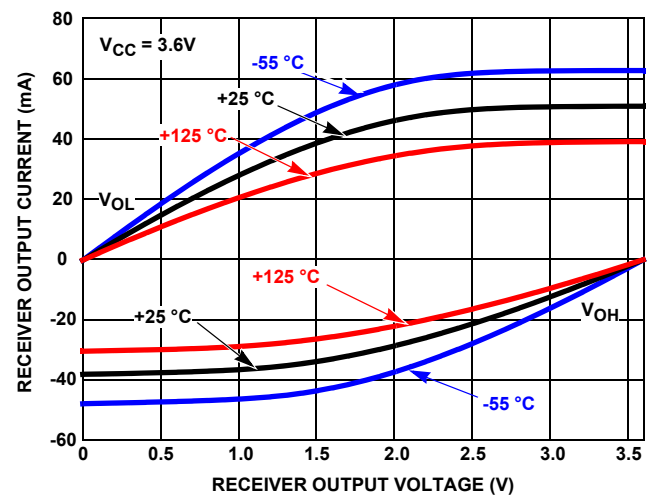


FIGURE 37. RECEIVER OUTPUT CURRENT vs RECEIVER OUTPUT VOLTAGE AT $V_{CC} = 3.6\text{V}$

Typical Performance Curves $C_L = 15\text{pF}$, $T_A = +25^\circ\text{C}$; unless otherwise specified. (Continued)

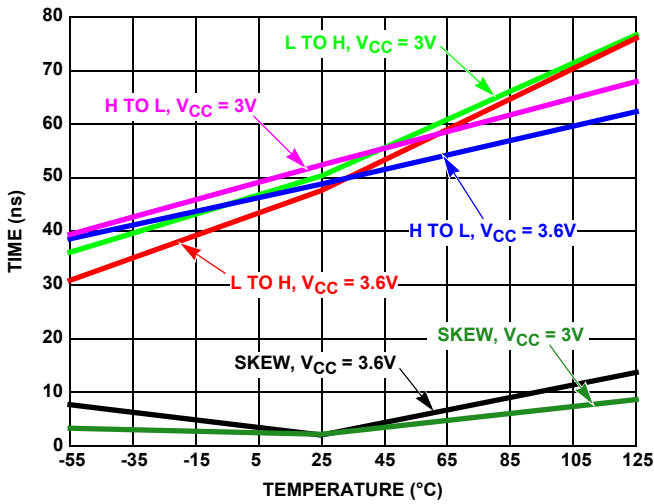


FIGURE 38. RECEIVER PROPAGATION DELAY AND SKEW vs TEMPERATURE

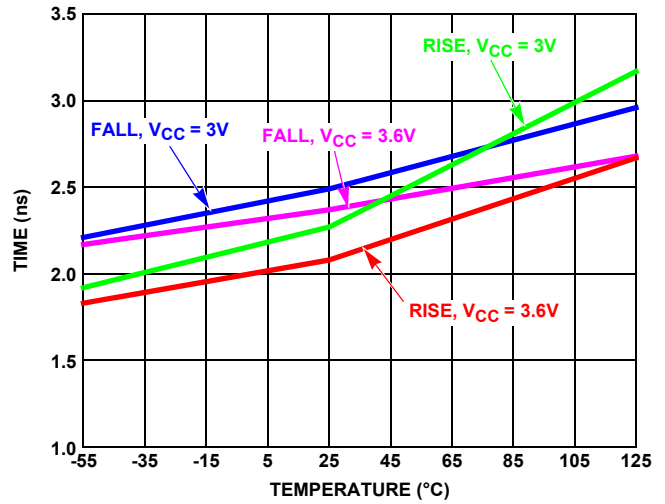


FIGURE 39. RECEIVER RISE AND FALL TIMES vs TEMPERATURE

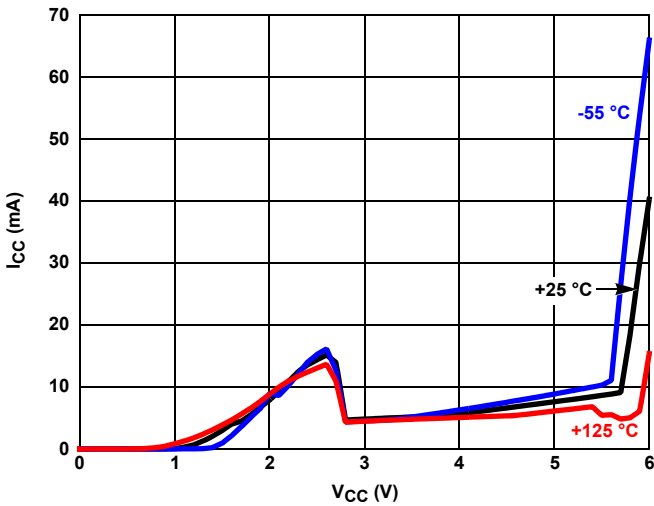


FIGURE 40. SUPPLY CURRENT vs SUPPLY VOLTAGE vs TEMPERATURE

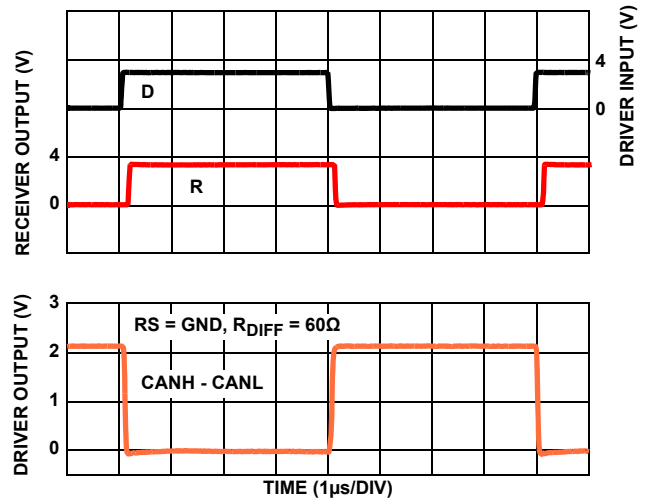


FIGURE 41. FAST DRIVER AND RECEIVER WAVEFORMS

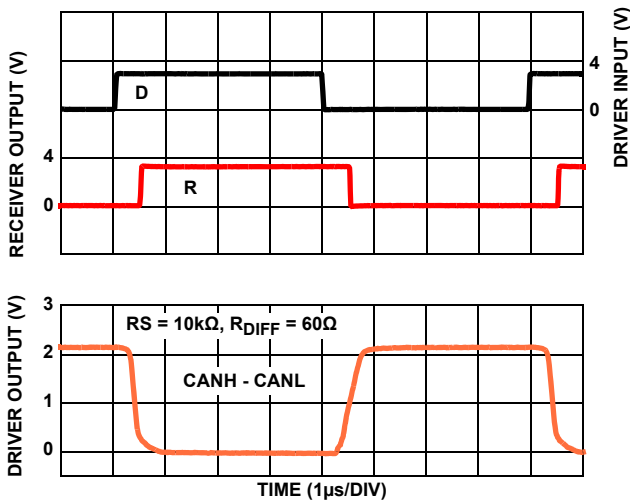


FIGURE 42. MEDIUM DRIVER AND RECEIVER WAVEFORMS

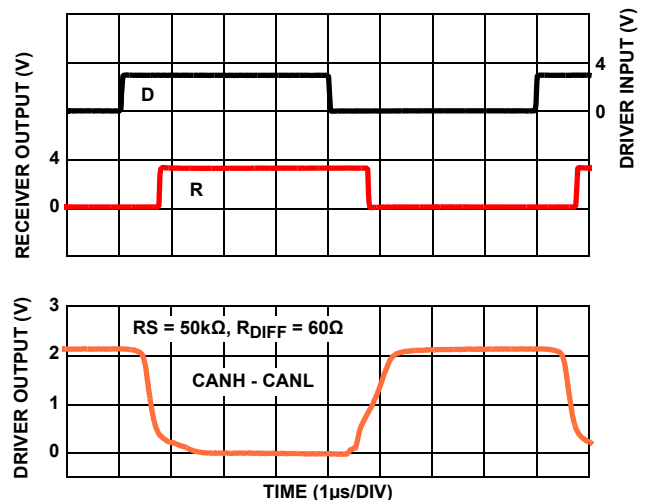


FIGURE 43. SLOW DRIVER AND RECEIVER WAVEFORMS

Die Characteristics

Die Dimensions

2413µm x 3322µm (95 mils x 130.79 mils)
 Thickness: 305µm ±25µm (12 mils ±1 mil)

Interface Materials

GLASSIVATION

Type: 12kÅ Silicon Nitride on 3kÅ Oxide

TOP METALLIZATION

Type: 300Å TiN on 2.8µm AlCu
 In Bondpads, TiN has been removed.

BACKSIDE FINISH

Silicon

PROCESS

P6SOI

Assembly Related Information

SUBSTRATE POTENTIAL

Floating

Additional Information

WORST CASE CURRENT DENSITY

$1.6 \times 10^5 \text{ A/cm}^2$

TRANSISTOR COUNT

4055

Weight of Packaged Device

0.31 grams

Lid Characteristics

Finish: Gold

Potential: Grounded, tied to package pin 2

Metalization Mask Layout

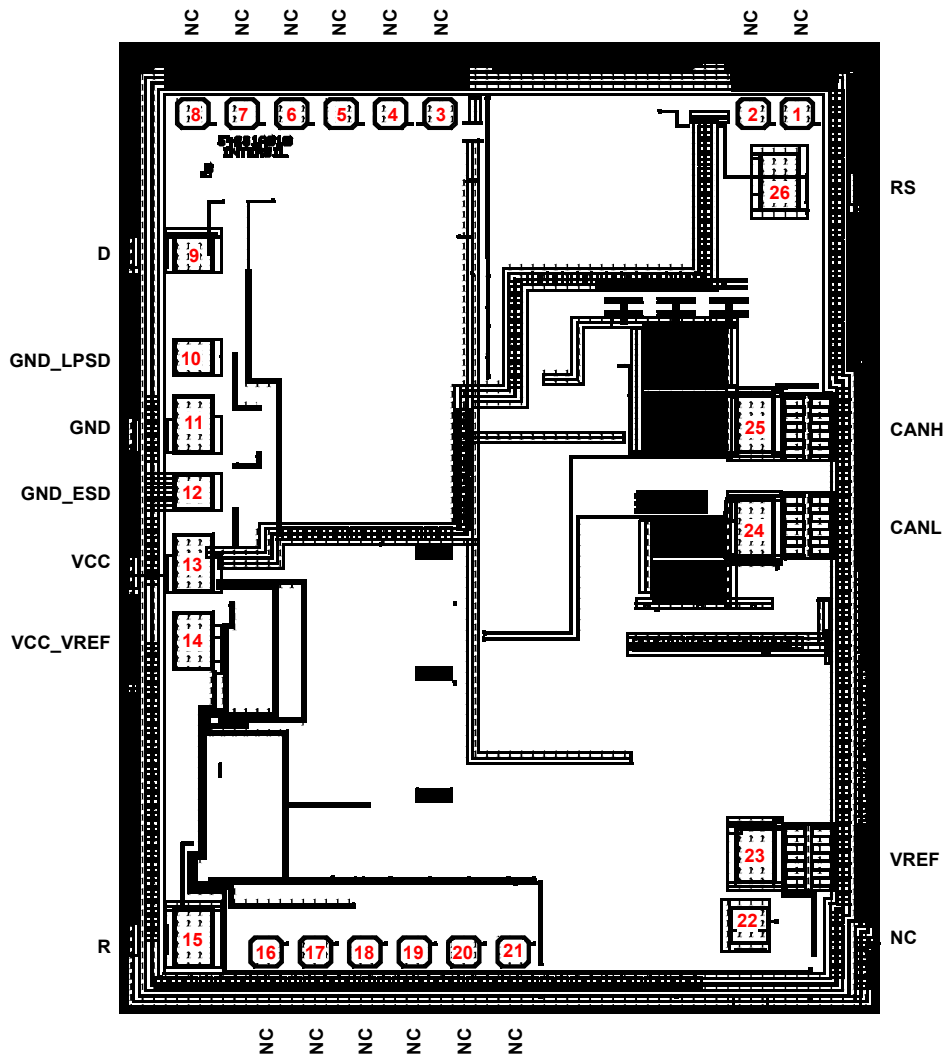


TABLE 2. ISL72028SEH DIE LAYOUT X-Y COORDINATES

| PAD NUMBER | PAD NAME | X (μm) | Y (μm) | X | Y |
|------------|----------|------------------------|------------------------|---------|----------|
| 1 | NC | 90.0 | 90.0 | 901.4 | 1365.6 |
| 2 | NC | 90.0 | 90.0 | 767.4 | 1365.6 |
| 3 | NC | 90.0 | 90.0 | -183.23 | 1365.6 |
| 4 | NC | 90.0 | 90.0 | -333.25 | 1365.6 |
| 5 | NC | 90.0 | 90.0 | -483.25 | 1365.6 |
| 6 | NC | 90.0 | 90.0 | -633.25 | 1365.6 |
| 7 | NC | 90.0 | 90.0 | -783.25 | 1365.6 |
| 8 | NC | 90.0 | 90.0 | -933.25 | 1365.6 |
| 9 | D | 110.0 | 110.0 | -931.1 | 901.85 |
| 10 | GND_LSPD | 110.0 | 110.0 | -931.1 | 563.25 |
| 11 | GND | 110.0 | 180.0 | -931.1 | 342.25 |
| 12 | GND_ESD | 110.0 | 110.05 | -931.1 | 119.42 |
| 13 | VCC | 110.0 | 180.0 | -931.1 | -115.05 |
| 14 | VCC_VREF | 110.0 | 180.05 | -931.1 | -371.08 |
| 15 | R | 110.0 | 180.0 | -931.1 | -1350.0 |
| 16 | NC | 90.0 | 90.0 | -711.1 | -1394.95 |
| 17 | NC | 90.0 | 90.0 | -561.1 | -1394.95 |
| 18 | NC | 90.0 | 90.0 | -411.1 | -1394.95 |
| 19 | NC | 90.0 | 90.0 | -261.1 | -1394.95 |
| 20 | NC | 90.0 | 90.0 | -111.1 | -1394.95 |
| 21 | NC | 90.0 | 90.0 | 38.9 | -1394.95 |
| 22 | NC | 110.0 | 110.0 | 756.9 | -1307.3 |
| 23 | VREF | 110.0 | 180.0 | 775.3 | -1072.3 |
| 24 | CANL | 110.0 | 180.0 | 772.1 | 2.15 |
| 25 | CANH | 110.0 | 180.05 | 772.1 | 343.33 |
| 26 | RS | 110.0 | 180.0 | 848.1 | 1140.6 |

NOTE: Origin of coordinates is the center of the die. NC - No Connect

Revision History The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to the web to make sure that you have the latest revision.

| DATE | REVISION | CHANGE |
|------------------|----------|--|
| August 16, 2016 | FN8764.3 | "Absolute Maximum Ratings" on page 4 changed voltage value in VCC to GND With/Without Ion Beam From: -0.3V to 4.5V To: -0.3V to 5.5V. |
| April 28, 2016 | FN8764.2 | - Updated title. - Updated the test condition for Output Rise Time on page 6. - Changed maximum data rate from 1Mbps to 5Mbps in the following locations: - Second paragraph and "Features" section on page 1. - In "Overview" on page 10. |
| November 9, 2015 | FN8764.1 | Absolute Maximum Ratings table on page 4: changed the value for "CANH, CANL, VREF Under Ion Beam" from $\pm 16V$ to $\pm 18V$. |
| October 26, 2015 | FN8764.0 | Initial Release |

About Intersil

Intersil Corporation is a leading provider of innovative power management and precision analog solutions. The company's products address some of the largest markets within the industrial and infrastructure, mobile computing and high-end consumer markets.

For the most updated datasheet, application notes, related documentation and related parts, please see the respective product information page found at www.intersil.com.

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Reliability reports are also available from our website at www.intersil.com/support.

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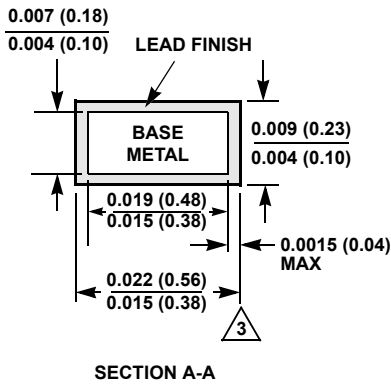
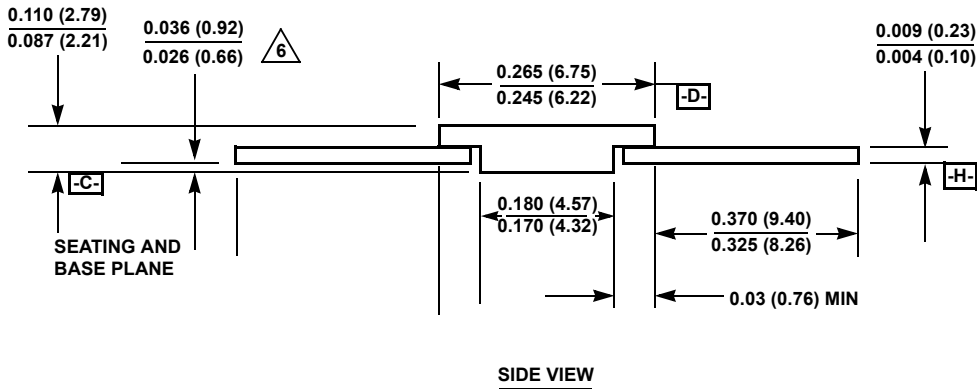
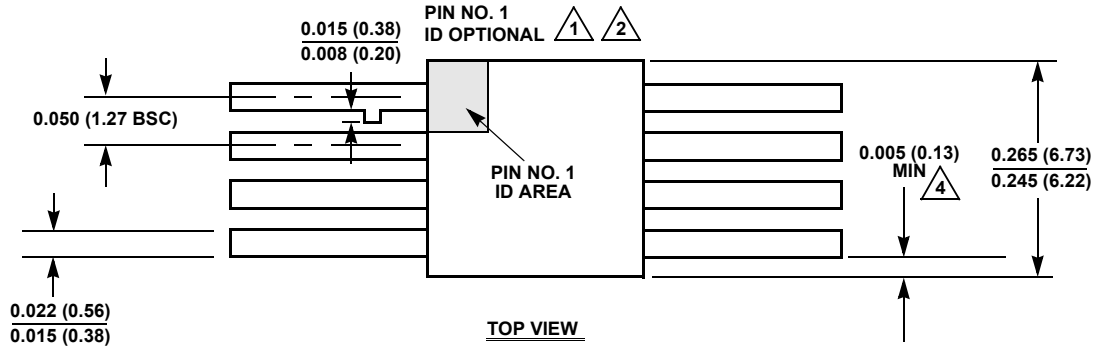
For information regarding Intersil Corporation and its products, see www.intersil.com

Package Outline Drawing

K8.A

8 LEAD CERAMIC METAL SEAL FLATPACK PACKAGE

Rev 4, 12/14



NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternately, a tab may be used to identify pin one.
2. If a pin one identification mark is used in addition to or instead of a tab, the limits of the tab dimension do not apply.
3. The maximum limits of lead dimensions (section A-A) shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
4. Measure dimension at all four corners.
5. For bottom-brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
6. Dimension shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension minimum shall be reduced by 0.0015 inch (0.038mm) maximum when solder dip lead finish is applied.
7. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
8. Controlling dimension: INCH.